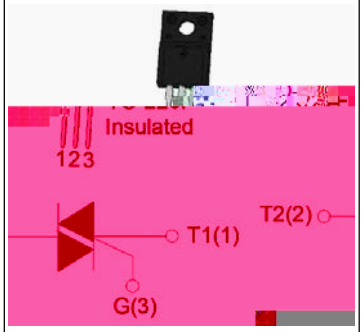
JST20F-800BW 20A TRIAC

Rev.A.1.1

DESCRIPTION:

The JST20F-800BW triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. JST20F-800BW snubberless triac is especially recommended for use on inductive loads. By using an external plastic package, JST20F-800BW provides a rated insulation voltage of 2000 VRMS, complying with UL standards (File ref: E252906). Package TO-220F is RoHS compliant.



MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	20	A
V_{DRM} /V_{RRM}	800	V
I_{GT} / /	50/50/50	mA

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage junction temperature range	T_{stg}	-40-150	
Operating junction temperature range	T_j	-40-125	
Repetitive peak off-state voltage (T_j=25)	V_{DRM}	800	V
Repetitive peak reverse voltage (T_j=25)	V_{RRM}	800	V
RMS on-state current ($T_C \leq$ 67)	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current (full cycle , t_p=20ms , T_j=25)	I_{TSM}	200	A
Non repetitive surge peak on-state current (full cycle , t_p=16.6ms , T_j=25)		220	
I^2t value for fusing (t_p=10ms , T_j=25)	I^2t	200	A^2s
Critical rate of rise of on-state current (I_G=2 × I_{GT} , f=100Hz , T_j=125)	dI/dt	100	A/μs
Peak gate current (t_p=20μs , T_j=125)	I_{GM}	4	A
Average gate power dissipation (T_j=125)	$P_{G(AV)}$	0.5	W

Peak gate power	P_{GM}	10	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	3.8	kV

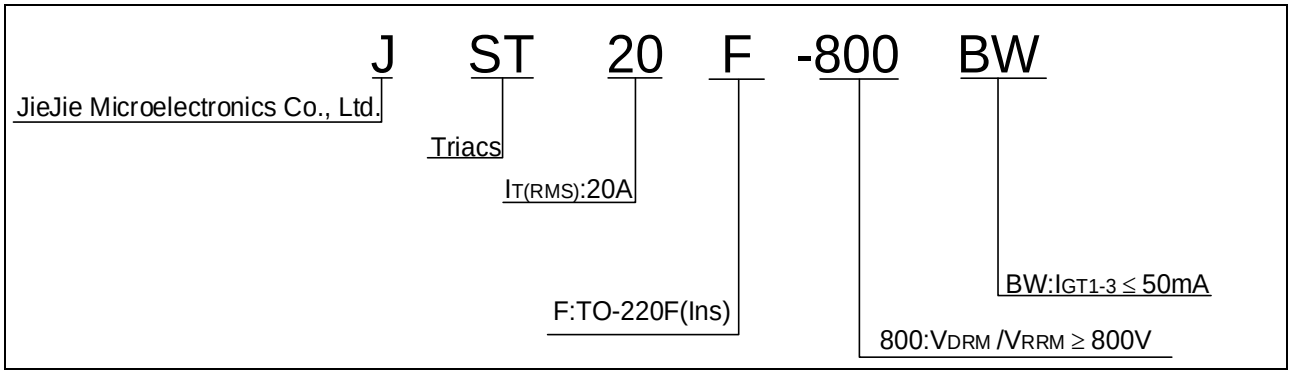
ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
I_{GT}	V_D =12V R_L =33Ω	- -	MAX.	50	mA
V_{GT}		- -	MAX.	1	V
V_{GD}	V_D =V_{DRM} T_j =125 R_L =3.3kΩ	- -	MIN.	0.2	V
I_L	I_G =1.2I_{GT}	-	MAX.	60	mA
				80	
I_H	I_T =500mA		MAX.	60	mA
dV/dt	V_D=540V Gate Open T_j =125		MIN.	2000	V/μs
(dI/dt)c	(dV/dt)c=20V/μs T_j=125		MIN.	25	A/ms
t_{on}	I_G=80mA I_A=400mA I_R=40mA T_j=25		TYP.	10	μs
t_{off}				70	

STATIC CHARACTERISTICS

Symbol	Parameter		Value(MAX.)	Unit
V_{TM}	I_{TM} =28A t_p=380μs	T_j=25	1.4	V
V_{TO}	Threshold voltage	T_j=125	0.75	V
R_D	Dynamic resistance	T_j=125		

ORDERING INFORMATION



MARKING

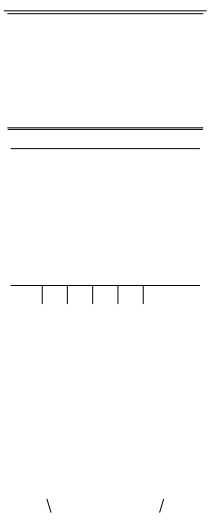


FIG.1: Maximum power dissipation versus RMS on-state current

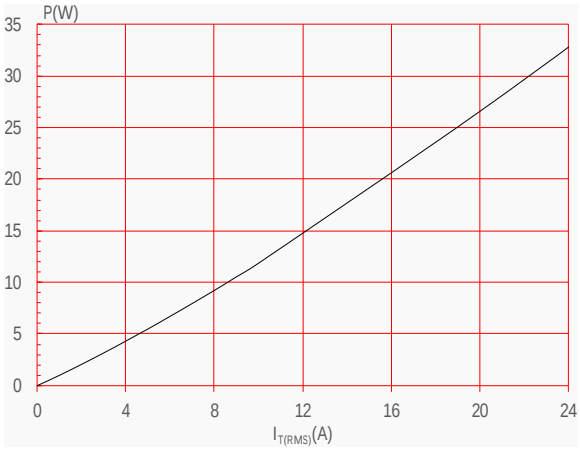


FIG.2: RMS on-state current versus case temperature

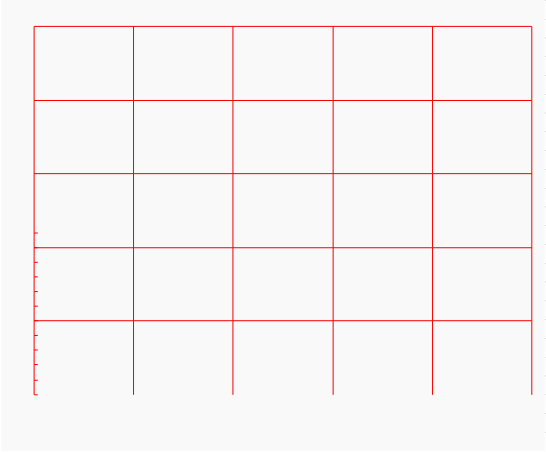
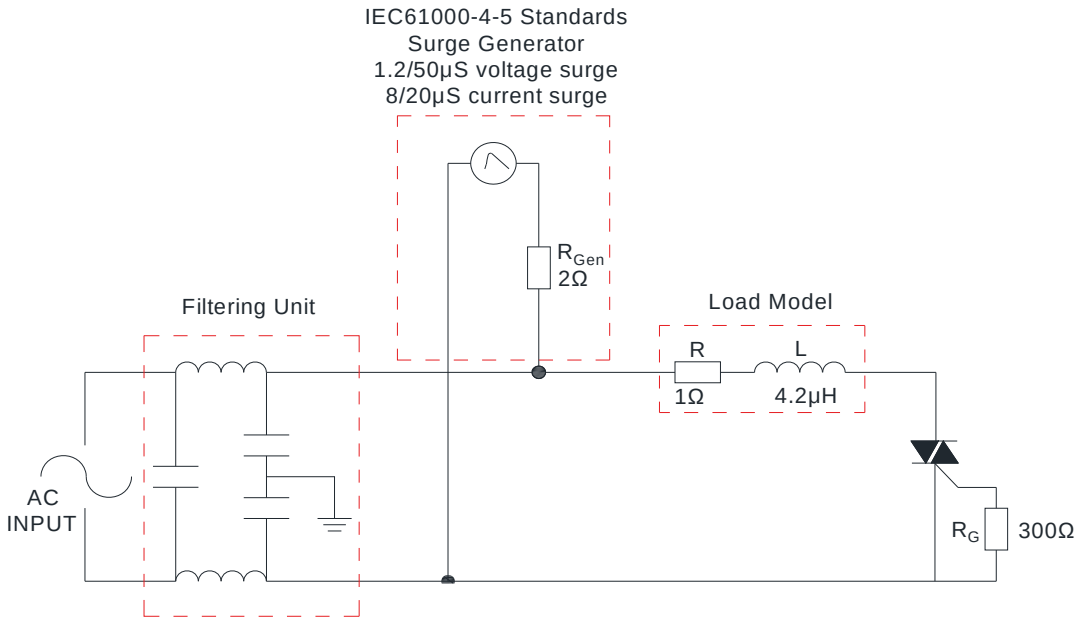


FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
		H- I- J			
JST20F-800BW	800	50	TO-220F(Ins)	50	Tube

Document Revision History

Date	Revision	Changes
Apr.12, 2023	A.1.0	Last updated
Oct.13, 2025	A.1.1	Revise PACKAGE MECHANICAL DATA

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